

**isc N-Channel MOSFET Transistor IPD082N10N3, IIPD082N10N3**

**• FEATURES**

- Static drain-source on-resistance:  
 $R_{DS(on)} \leq 8.2m\Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**• DESCRIPTION**

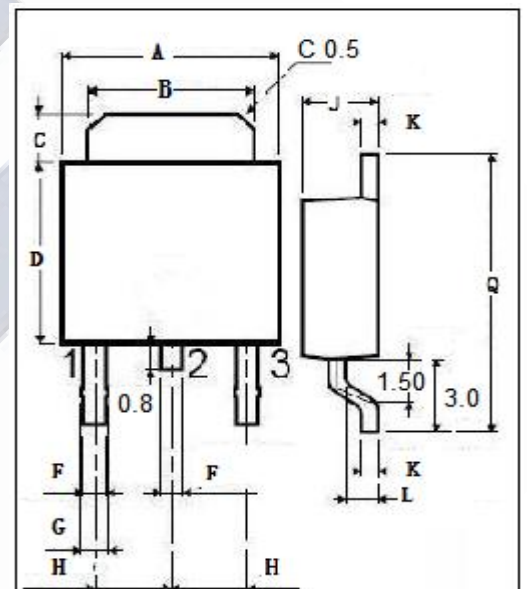
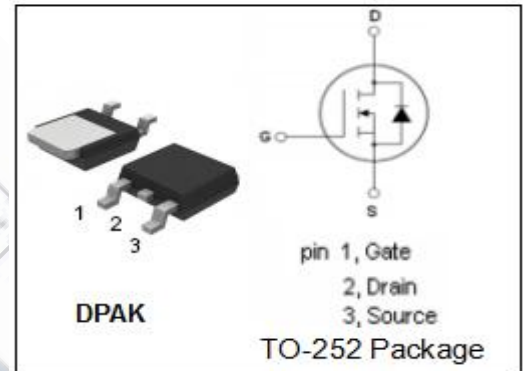
- Ideal for high-frequency switching and synchronous rectification

**• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	80	A
$I_{DM}$	Drain Current-Single Pulsed	320	A
$P_D$	Total Dissipation @ $T_c=25^\circ C$	125	W
$T_j$	Max. Operating Junction Temperature	175	$^\circ C$
$T_{stg}$	Storage Temperature	-55~175	$^\circ C$

**• THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Channel-to-case thermal resistance	1.2	$^\circ C/W$
$R_{th(j-a)}$	Channel-to-ambient thermal resistance	62	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

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**ELECTRICAL CHARACTERISTICS**

 T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =1mA	100			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =75 μA	2		3.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =73A			8.2	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = 20V; V <sub>DS</sub> =0V			0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V; V <sub>GS</sub> = 0V			1	μA
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> =80A, V <sub>GS</sub> = 0V			1.2	V